

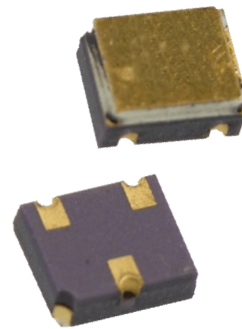
Surface Mount NP General Purpose Transistor



2N2907AUB (TX, TXV)

Features:

- Ceramic 3 pin surface mount package (UBN)
- Miniature package to minimize circuit board area
- Hermetically sealed
- Footprint and pin-out matches SOT-23 package transistors
- Processed per MIL-PRF-19500/291



Description:

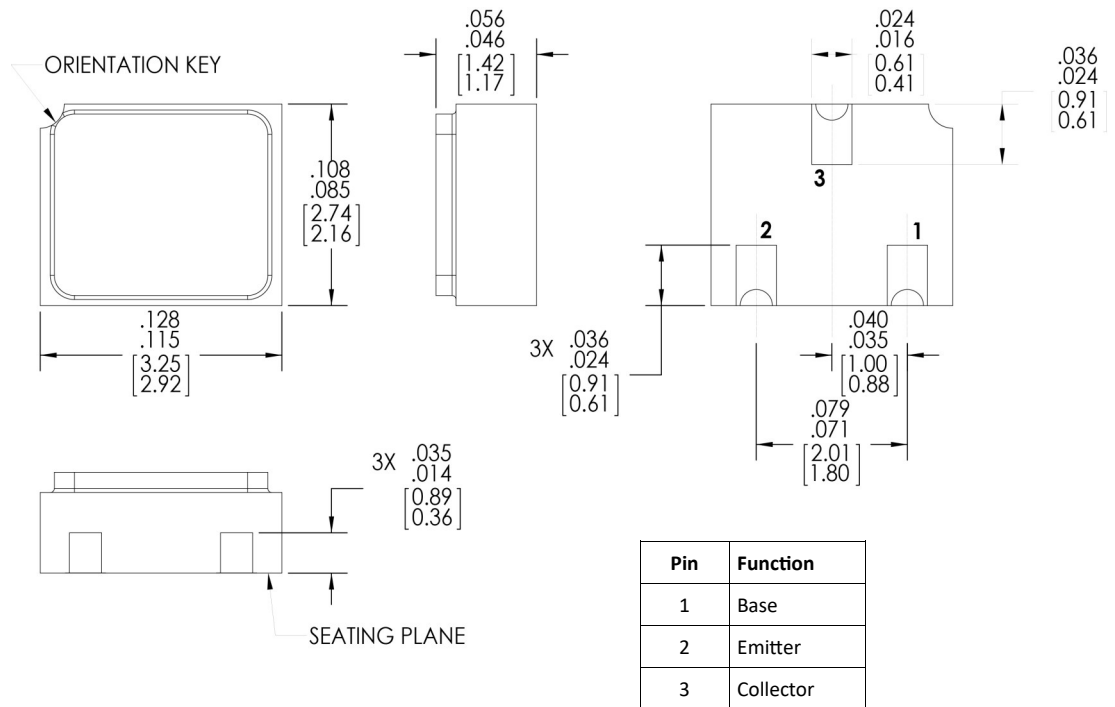
The 2N2907AUB, 2N2907AUBTX and 2N2907AUBTXV are miniature, hermetically sealed, ceramic surface mount general purpose switching transistors. The miniature three pin ceramic package is ideal for upgrading commercial grade circuits to military reliability levels where plastic SOT-23 devices have been used. The "UB" suffix denotes the 3 terminal chip carrier package, type "B" per MIL-PRF-19500/291.

Typical screening and lot acceptance tests per MIL-PRF-19500/291.
 The burn-in condition is $V_{CB} = 30\text{ V}$, $P_D = 200\text{ mW}$, $T_A = 25^\circ\text{C}$, $t = 80\text{ hrs}$.

Refer to MIL-PRF-19500/291 for complete requirements. In addition, the TX and TXV versions receive 100% thermal response testing.

Applications:

- General switching
- Amplification
- Signal processing
- Radio transmission
- Logic gates



General Note
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Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)	
Collector-Base Voltage	60V
Collector-Emitter Voltage	60V
Emitter-Base Voltage	5.0V
Collector Current-Continuous	600mA
Operating Junction Temperature (T_J)	-65°C to $+200^\circ\text{C}$
Storage Junction Temperature (T_{stg})	-65°C to $+200^\circ\text{C}$
Power Dissipation @ $T_A = 25^\circ\text{C}$	0.5 W
Power Dissipation @ $T_c = 25^\circ\text{C}$	1.00 W ⁽¹⁾
Soldering Temperature (vapor phase reflow for 30 seconds)	215° C
Soldering Temperature (heated collet for 5 seconds)	260° C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
OFF CHARACTERISTICS					
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	60	-	V	$I_C = 10\ \mu\text{A}, I_E = 0$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	60	-	V	$I_C = 10\ \text{mA}, I_B = 0^{(2)}$
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5.0	-	V	$I_E = 10\ \mu\text{A}, I_C = 0$
I_{CBO}	Collector-Base Cutoff Current		10	μA	$V_{CB} = 50\ \text{V}, I_E = 0$
			10	μA	$V_{CB} = 50\ \text{V}, I_E = 0, T_A = 150^\circ\text{C}$
I_{EBO}	Emitter-Base Cutoff Current		10	μA	$V_{CE} = 4.0\ \text{V}, I_C = 0$
I_{CES}	Collector Emitter Cutoff Current		10	nA	$V_{EB} = 50\ \text{V}$
ON CHARACTERISTICS					
h_{FE}	Forward-Current Transfer Ratio	75		-	$V_{CE} = 10\ \text{V}, I_C = 0.1\ \text{mA}$
		100	450	-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}$
		100		-	$V_{CE} = 10\ \text{V}, I_C = 10\ \text{mA}$
		100	300	-	$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}^{(2)}$
		50		-	$V_{CE} = 10\ \text{V}, I_C = 500\ \text{mA}^{(2)}$
		50		-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}, T_A = -55^\circ\text{C}$

Note:

- Derate linearly 6.6 mW/°C above 25° C
- Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

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2N2907AUB (TX, TXV)

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
ON CHARACTERISTICS					
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage		0.40	V	$I_C = 150\text{ mA}, I_B = 15\text{ mA}^{(2)}$
			1.60	V	$I_C = 500\text{ mA}, I_B = 50\text{ mA}^{(2)}$
$V_{BE(SAT)}$	Base-Emitter Saturation Voltage		1.30	V	$I_C = 150\text{ mA}, I_B = 15\text{ mA}^{(2)}$
			2.60	V	$I_C = 500\text{ mA}, I_B = 50\text{ mA}^{(2)}$
SMALL-SIGNAL CHARACTERISTICS					
$ h_{fe} $	Small Signal Forward Current Transfer Ratio	100		-	$V_{CE} = 10\text{ V}, I_C = 1.0\text{ mA}, f = 1.0\text{ kHz}$
$ h_{fe} $	Small Signal Forward Current Transfer Ratio	2.0		-	$V_{CE} = 20\text{ V}, I_C = 20\text{ mA}, f = 100\text{ MHz}$
C_{obo}	Open Circuit Output Capacitance		8.0	pF	$V_{CB} = 10\text{ V}, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$
C_{ibo}	Input Capacitance (Output Open)		30	pF	$V_{EB} = 2.0\text{ V}, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$
SWITCHING CHARACTERISTICS					
t_{on}	Turn-On Time		45	ns	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$
t_{off}	Turn-Off Time		300	ns	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = I_{B2} = 15\text{ mA}$

Note:

1. Derate linearly 6.6 mW/°C above 25° C
2. Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

General Note

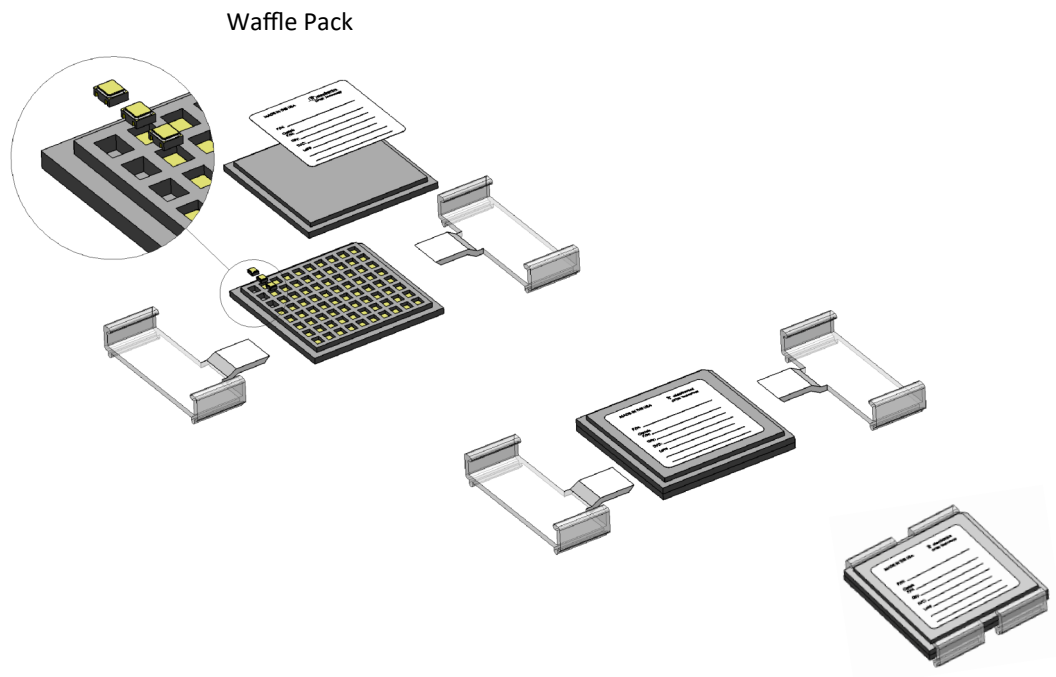
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Standard Packaging:



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